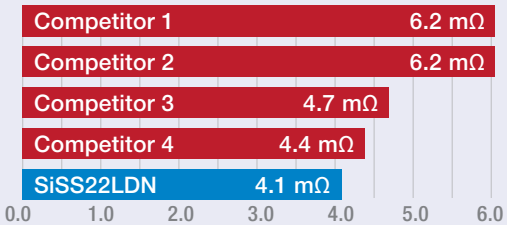
SiSS22LDN TrenchFET® GEN IV POWER MOSFET

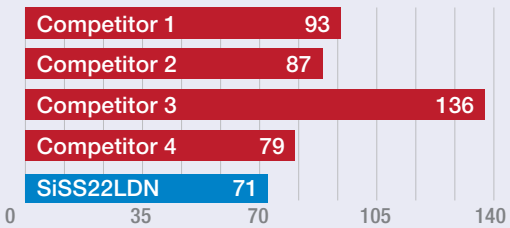
V_{DS} = 60 V in PowerPAK® 1212-8S

$R_{DS(on)}$ AT V_{GS} = 4.5 V (TYPICAL)



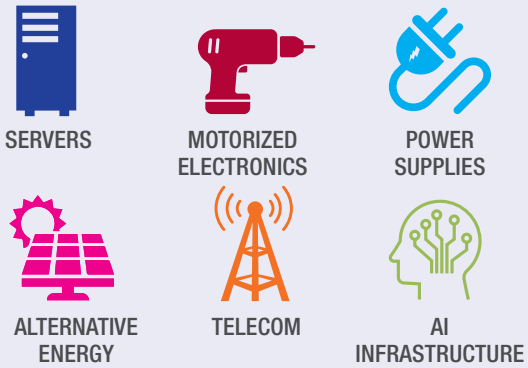
- The lowest $R_{DS(on)}$ in its class
- Typical $R_{DS(on)}$ at 4.5 V = 4.1 mΩ
- Typical $R_{DS(on)}$ at 10 V = 2.91 mΩ
- Reduces conduction loss and increases power density

$R_{DS(on)}$-Q_g FOM (mΩ) AT 4.5 V



- Excellent R_{DS}-Q_{oss} FOM is optimized for synchronous rectification
- R_{DS}-Q_g FOM for V_{GS} of 4.5 V is 10 % lower than the next best product
- Very low Q_{oss} cut unplanned power loss during diode conduction

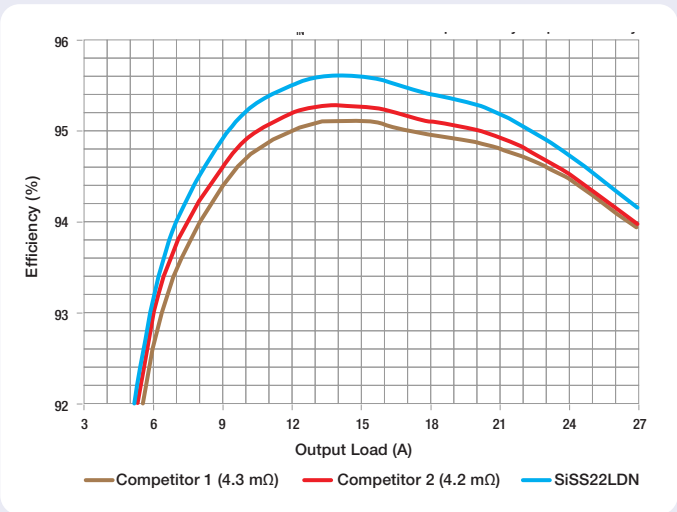
TARGET APPLICATIONS



ENABLES HIGHER EFFICIENCY

- Achieves higher efficiency
- Drop-in upgrade and conventional package type
- Efficiency comparison (right) shows SiSS22LDN and competitor test results on 1/8 brick with V_{IN} = 48 V, V_{OUT} = 3.3 V, F_{sw} = 140 kHz, and using four devices for secondary side synchronous rectification

SiSS22LDN AND HIGH PERFORMANCE COMPETITORS: EFFICIENCY vs. LOAD



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